8A, 400V - 600V Ultrafast Diodes

The RURD840, RURD860, RURD840S and RURD860S are ultrafast dual diodes with soft recovery characteristics (t_{rr} < 60ns). They have low forward voltage drop and are silicon nitride passivated ion-implanted epitaxial planar construction.

These devices are intended for use as freewheeling/ clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and ultrafast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Formerly developmental type TA09616.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RURD840	TO-251	RUR840
RURD860	TO-251	RUR860
RURD840S	TO-252	RUR840
RURD860S	TO-252	RUR860

NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-252 variant in tape and reel, e.g. RURD860S9A.

Symbol



Features

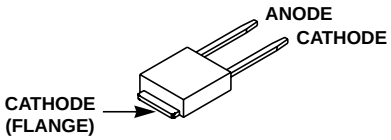
- Ultrafast with Soft Recovery . . . . . <60ns
- Operating Temperature. . . . . .175^{o}C
- Reverse Voltage Up To 600V
- Avalanche Energy Rated
- Planar Construction

Applications

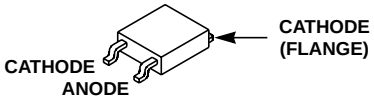
- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Packaging

JEDEC STYLE TO-251



JEDEC STYLE TO-252



Absolute Maximum Ratings T_C = 25^{o}C, Unless Otherwise Specified

		RURD840 RURD840S	RURD860 RURD860S	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	400	600	V
Working Peak Reverse Voltage	V_{RWM}	400	600	V
DC Blocking Voltage	V_R	400	600	V
Average Rectified Forward Current (T_C = 155^{o}C)	$I_{F(AV)}$	8	8	A
Repetitive Peak Surge Current (Square Wave, 20kHz)	I_{FRM}	16	16	A
Nonrepetitive Peak Surge Current (Halfwave, 1 Phase, 60Hz)	I_{FSM}	40	40	A
Maximum Power Dissipation	P_D	75	75	W
Avalanche Energy (See Figures 10 and 11)	E_{AVL}	20	20	mJ
Operating and Storage Temperature	T_{STG}, T_J	-65 to 175	-65 to 175	^{o}C
Maximum Lead Temperature for Soldering				
Leads at 0.063in (1.6mm) from Case for 10s	T_L	300	300	^{o}C
Package Body for 10s, See Tech Brief 334	T_{PKG}	260	260	^{o}C

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Electrical Specifications $T_C = 25^oC$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	RURD840, RURD840S			RURD860, RURD860S			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
V_F	I_F = 8A	-	-	1.5	-	-	1.5	V
	I_F = 8A, $T_C = 150^oC$	-	-	1.3	-	-	1.3	V
I_R	V_R = 400V	-	-	100	-	-	-	µA
	V_R = 600V	-	-	-	-	-	100	µA
	V_R = 400V, $T_C = 150^oC$	-	-	500	-	-	-	µA
	V_R = 600V, $T_C = 150^oC$	-	-	-	-	-	500	µA
t_{rr}	I_F = 1A, dI_F/dt = 200A/µs	-	-	60	-	-	60	ns
	I_F = 8A, dI_F/dt = 200A/µs	-	-	70	-	-	70	ns
t_a	I_F = 8A, dI_F/dt = 200A/µs	-	32	-	-	32	-	ns
t_b	I_F = 8A, dI_F/dt = 200A/µs	-	21	-	-	21	-	ns
Q_{RR}	I_F = 8A, dI_F/dt = 200A/µs	-	195	-	-	195	-	nC
C_J	V_R = 10V, I_F = 0A	-	25	-	-	25	-	pF
$R_{\theta JC}$		-	-	2	-	-	2	$^oC/W$

DEFINITIONS

V_F = Instantaneous forward voltage (pw = 300µs, D = 2%).

I_R = Instantaneous reverse current.

t_{rr} = Reverse recovery time (See Figure 9), summation of $t_a + t_b$.

t_a = Time to reach peak reverse current (See Figure 9).

t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 9).

Q_{RR} = Reverse recovery charge.

C_J = Junction Capacitance.

$R_{\theta JC}$ = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

Typical Performance Curves

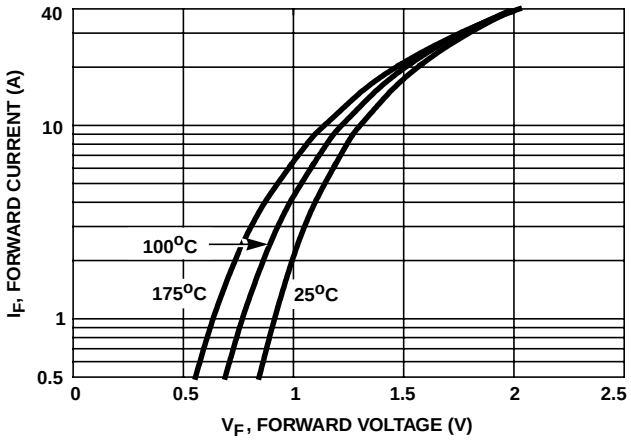


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

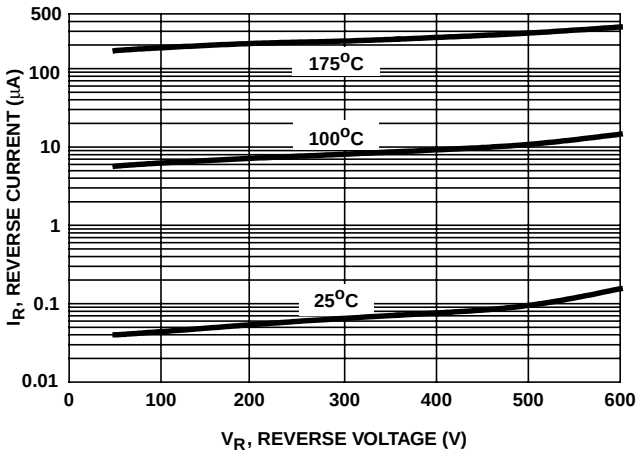


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

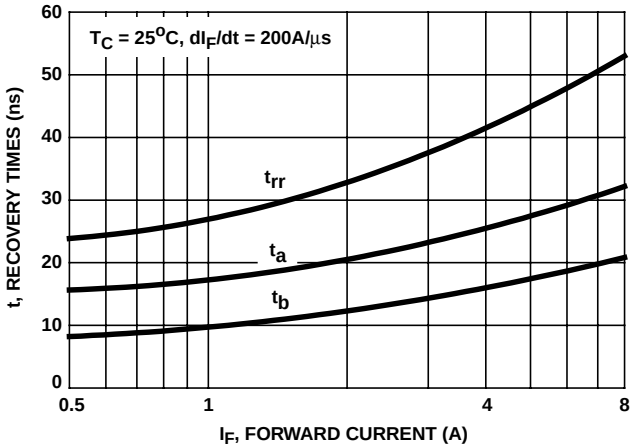


FIGURE 3. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

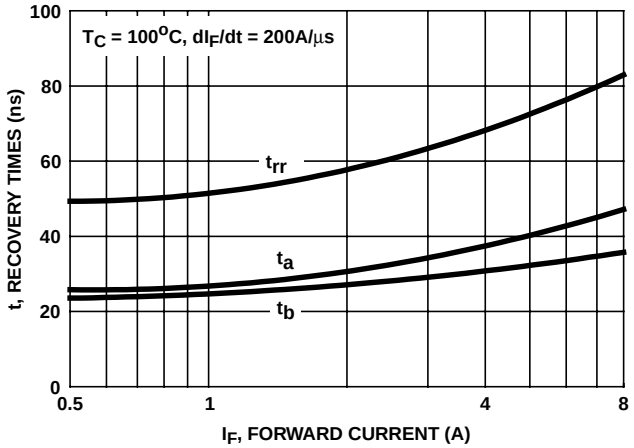


FIGURE 4. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

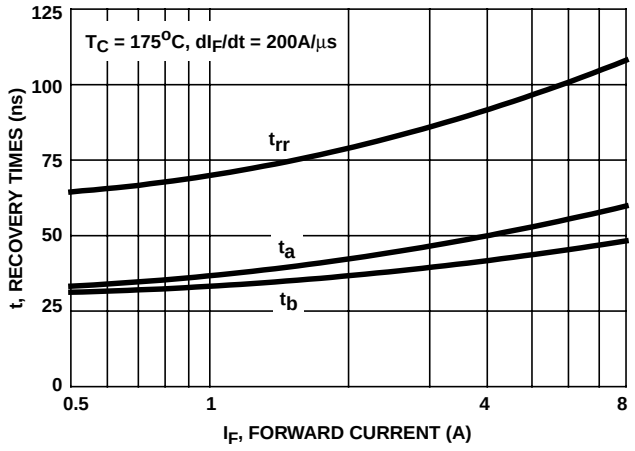


FIGURE 5. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

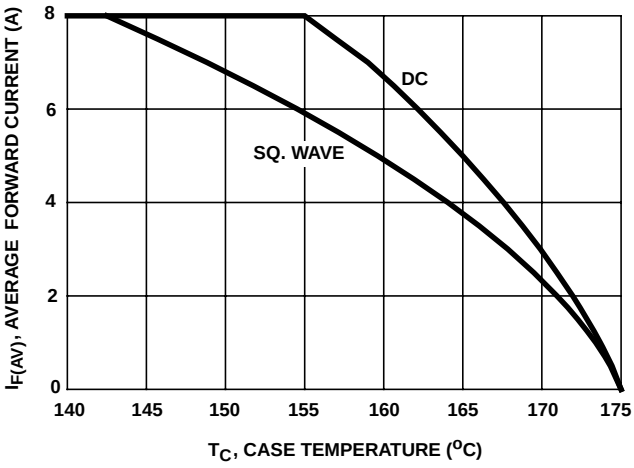


FIGURE 6. CURRENT DERATING CURVE

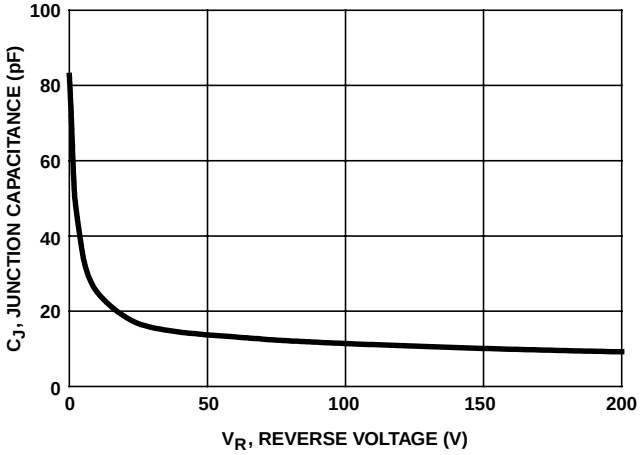


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

Test Circuits and Waveforms

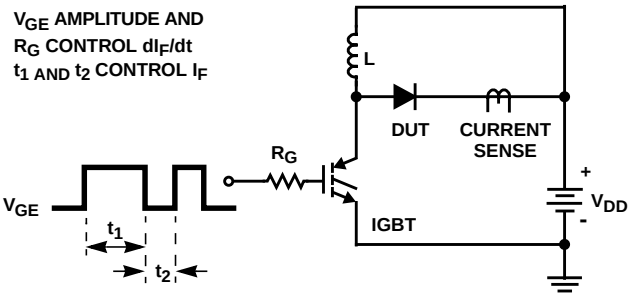


FIGURE 8. t_{rr} TEST CIRCUIT

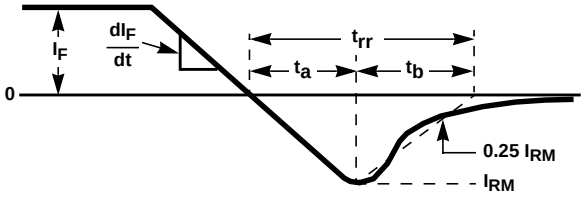


FIGURE 9. t_{rr} WAVEFORMS AND DEFINITIONS

I = 1A
L = 40mH
R < 0.1Ω
$E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$
Q_1 = IGBT (BV_{CES} > DUT $V_{R(AVL)}$)

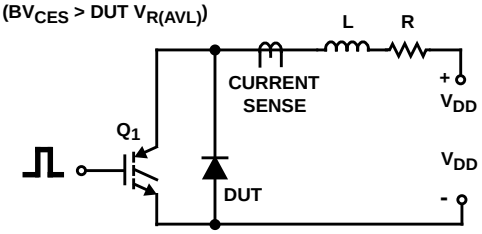


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

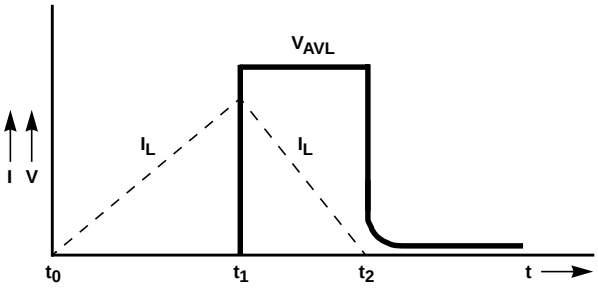


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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